

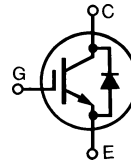
Low $V_{CE(sat)}$ IGBT with Diode High Speed IGBT with Diode

IXSH 30 N60U1
IXSH 30 N60AU1

V_{CES}	I_{C25}	$V_{CE(sat)}$
600 V	50 A	2.5 V
600 V	50 A	3.0 V

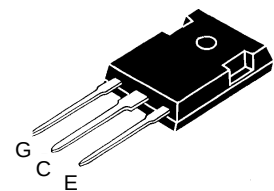
Combi Packs

Short Circuit SOA Capability



Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	600	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GE} = 1\text{ M}\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	50	A
I_{C90}	$T_C = 90^\circ\text{C}$	30	A
I_{CM}	$T_C = 25^\circ\text{C}$, 1 ms	100	A
SSOA (RBSOA)	$V_{GE} = 15\text{ V}$, $T_J = 125^\circ\text{C}$, $R_G = 33\ \Omega$ Clamped inductive load, $L = 100\ \mu\text{H}$	$I_{CM} = 60$ @ $0.8\ V_{CES}$	A
t_{SC} (SCSOA)	$V_{GE} = 15\text{ V}$, $V_{CE} = 360\text{ V}$, $T_J = 125^\circ\text{C}$ $R_G = 33\ \Omega$, non repetitive	10	μs
P_C	$T_C = 25^\circ\text{C}$	200	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
M_d	Mounting torque	1.13/10	Nm/lb.in.
Weight		6	g
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$

TO-247 AD



G = Gate,
E = Emitter,
C = Collector,
TAB = Collector

Features

- International standard package JEDEC TO-247 AD
- High frequency IGBT with guaranteed Short Circuit SOA capability
- IGBT and anti-parallel FRED in one package
- 2nd generation HDMOS™ process
- Low $V_{CE(sat)}$
 - for low on-state conduction losses
- MOS Gate turn-on
 - drive simplicity

Applications

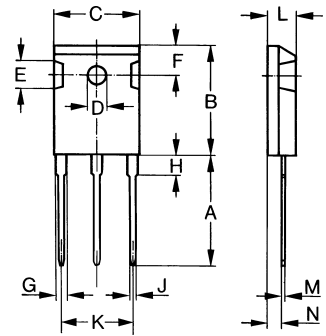
- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

Advantages

- Space savings (two devices in one package)
- Easy to mount with 1 screw (isolated mounting screw hole)
- Reduces assembly time and cost
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
BV_{CES}	$I_C = 750\ \mu\text{A}$, $V_{GE} = 0\text{ V}$	600		V
$V_{GE(th)}$	$I_C = 2.5\text{ mA}$, $V_{CE} = V_{GE}$	5		V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0\text{ V}$			500 μA 8 mA
I_{GES}	$V_{CE} = 0\text{ V}$, $V_{GE} = \pm 20\text{ V}$			$\pm 100\text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C90}$, $V_{GE} = 15\text{ V}$			2.5 V 3.0 V
				30N60U1 30N60AU1

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$I_C = I_{C90}, V_{CE} = 10\text{ V}$, Pulse test, $t \leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$	7	13	S
$I_{C(on)}$	$V_{GE} = 15\text{ V}$, $V_{CE} = 10\text{ V}$		100	A
C_{ies}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 1\text{ MHz}$		2760	pF
C_{oes}			240	pF
C_{res}			51	pF
Q_g	$I_C = I_{C90}, V_{GE} = 15\text{ V}$, $V_{CE} = 0.5 V_{CES}$		110	nC
Q_{ge}			34	nC
Q_{gc}			47	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = I_{C90}, V_{GE} = 15\text{ V}$, $L = 100\text{ }\mu\text{H}$, $V_{CE} = 0.8 V_{CES}$, $R_G = 4.7\text{ }\Omega$ Remarks: Switching times may increase for $V_{CE}(\text{Clamp}) > 0.8 \cdot V_{CES}$, higher T_J or increased R_G		60	ns
t_{ri}			130	ns
$t_{d(off)}$			400	ns
t_{fi}		30N60U1	400	ns
E_{off}		30N60AU1	200	ns
		30N60AU1	2.5	mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = I_{C90}, V_{GE} = 15\text{ V}$, $L = 100\text{ }\mu\text{H}$ $V_{CE} = 0.8 V_{CES}$, $R_G = 4.7\text{ }\Omega$ Remarks: Switching times may increase for $V_{CE}(\text{Clamp}) > 0.8 \cdot V_{CES}$, higher T_J or increased R_G		60	ns
t_{ri}			130	ns
E_{on}			4.2	mJ
$t_{d(off)}$		30N60U1	540	1000 ns
		30N60AU1	340	525 ns
t_{fi}		30N60U1	600	1500 ns
		30N60AU1	340	700 ns
E_{off}		30N60U1	12	mJ
		30N60AU1	6	mJ
R_{thJC}				0.63 K/W
R_{thCK}			0.25	K/W

TO-247 AD (IXSH) Outline


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	19.81	20.32	0.780	0.800
B	20.80	21.46	0.819	0.845
C	15.75	16.26	0.610	0.640
D	3.55	3.65	0.140	0.144
E	4.32	5.49	0.170	0.216
F	5.4	6.2	0.212	0.244
G	1.65	2.13	0.065	0.084
H	-	4.5	-	0.177
J	1.0	1.4	0.040	0.055
K	10.8	11.0	0.426	0.433
L	4.7	5.3	0.185	0.209
M	0.4	0.8	0.016	0.031
N	1.5	2.49	0.087	0.102

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_F	$I_F = I_{C90}, V_{GE} = 0\text{ V}$, Pulse test, $t \leq 300\text{ }\mu\text{s}$, duty cycle $d \leq 2\%$			1.6 V
I_{RM}	$I_F = I_{C90}, V_{GE} = 0\text{ V}$, $-di_F/dt = 240\text{ A}/\mu\text{s}$ $V_R = 360\text{ V}$ $I_F = 1\text{ A}$; $-di/dt = 100\text{ A}/\mu\text{s}$; $V_R = 30\text{ V}$		10	15 A
t_{rr}			150	ns
			35	50 ns
R_{thJC}				1 K/W

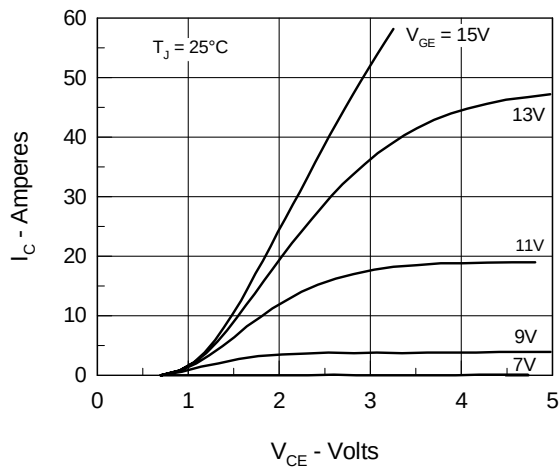
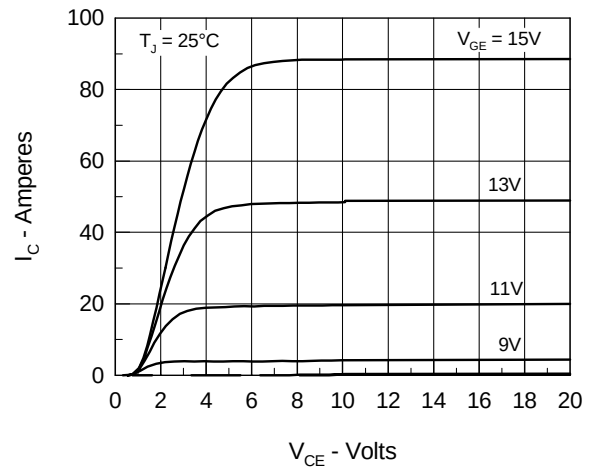
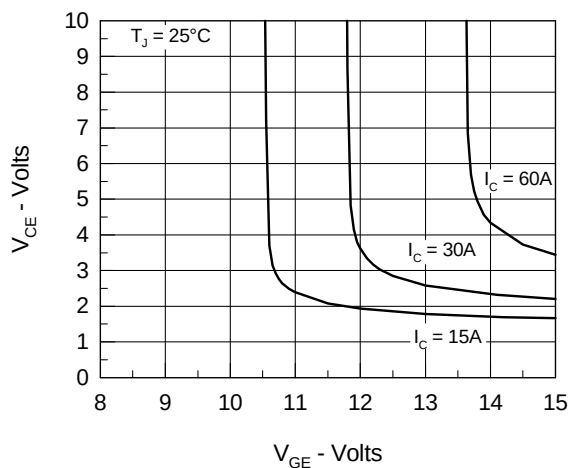
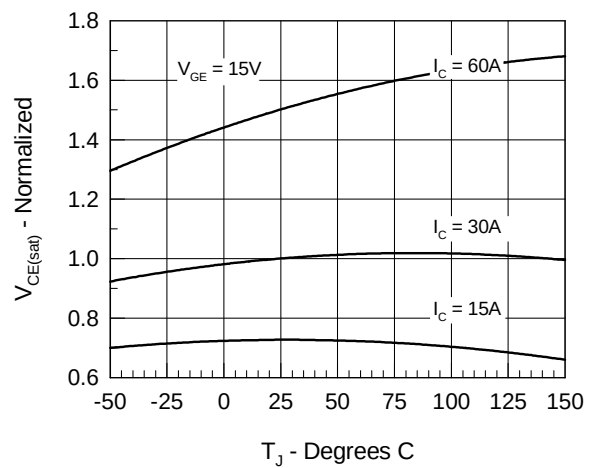
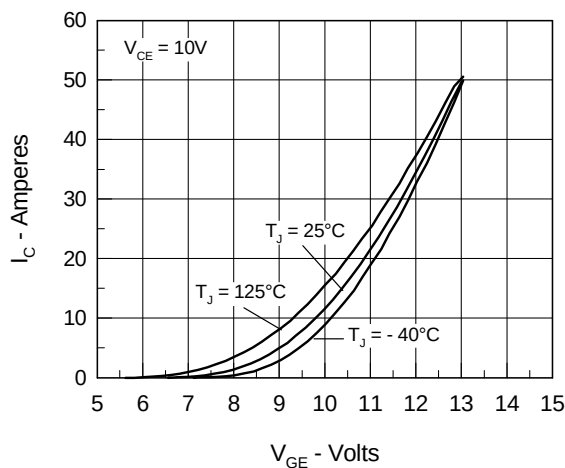
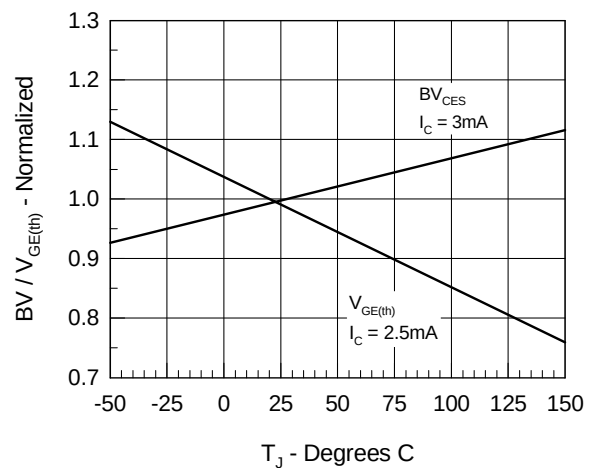
Fig.1 Saturation Characteristics

Fig.2 Output Characteristics

Fig.3 Collector-Emittter Voltage vs. Gate-Emittter Voltage

Fig.4 Temperature Dependence of Output Saturation Voltage

Fig.5 Input Admittance

Fig.6 Temperature Dependence of Breakdown and Threshold Voltage


Fig.7 Turn-Off Energy per Pulse and Fall Time on Collector Current

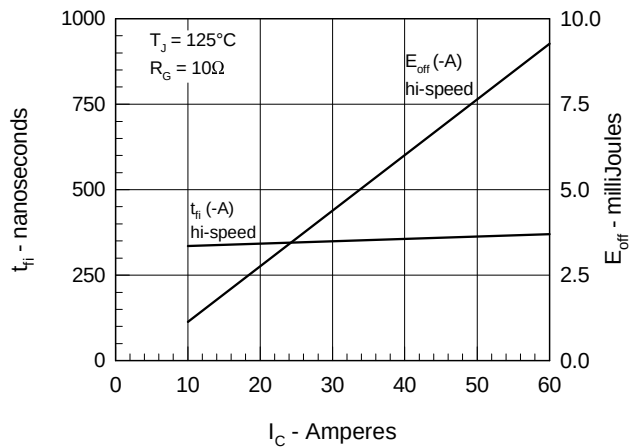


Fig.8 Dependence of Turn-Off Energy Per Pulse and Fall Time on R_G

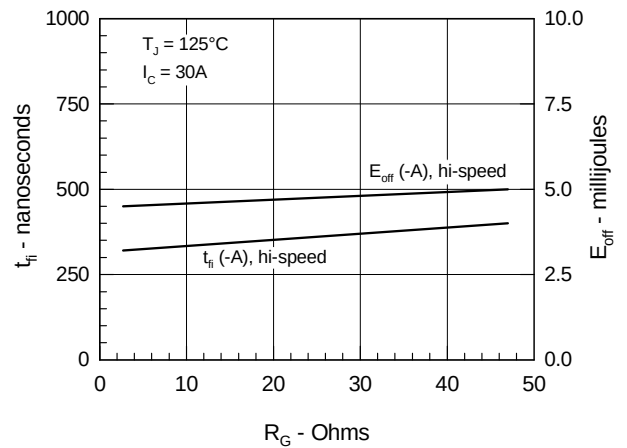


Fig.9 Gate Charge Characteristic Curve

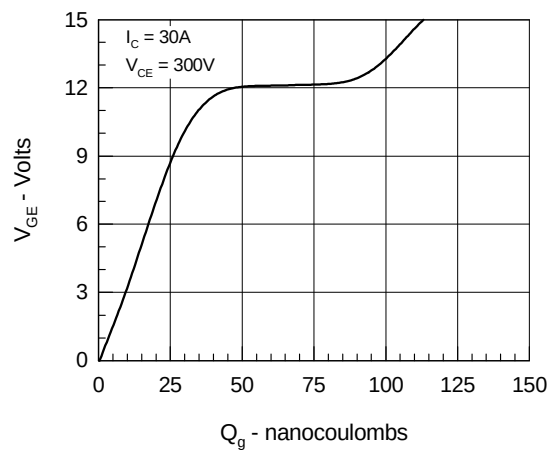


Fig.10 Turn-Off Safe Operating Area

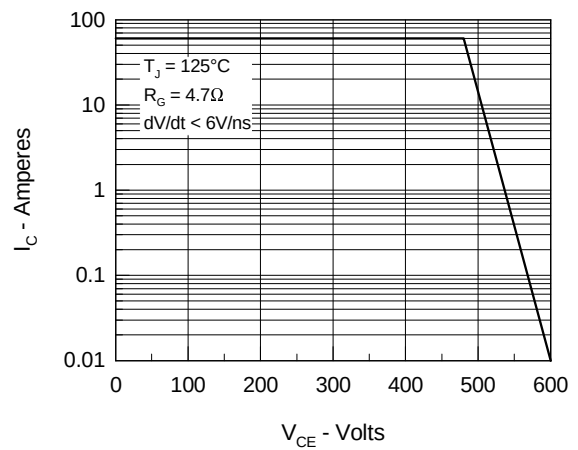


Fig.11 Transient Thermal Impedance

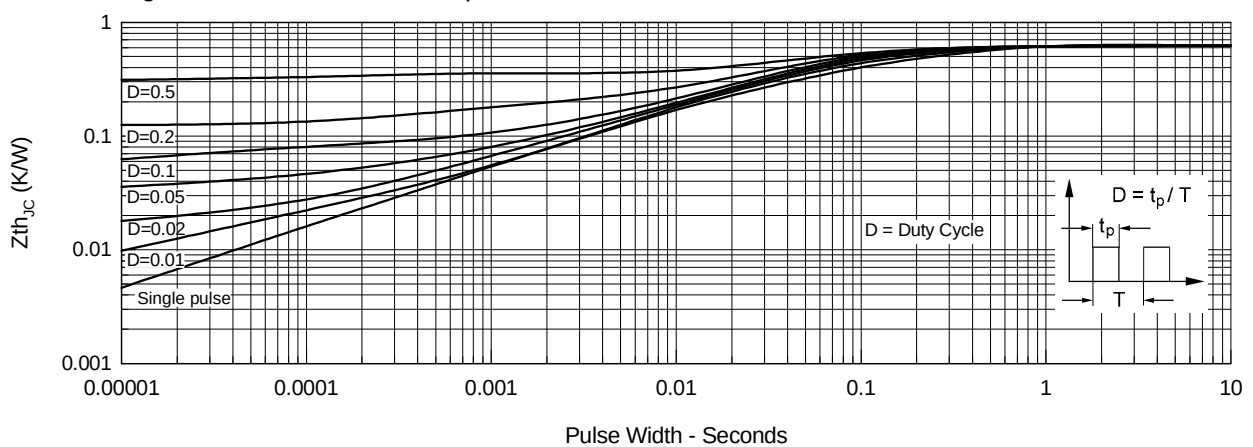


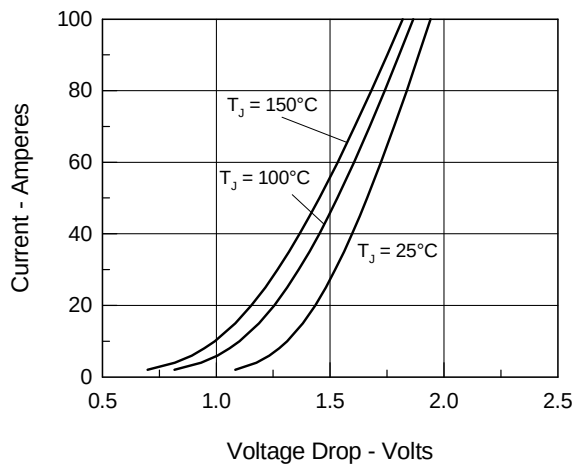
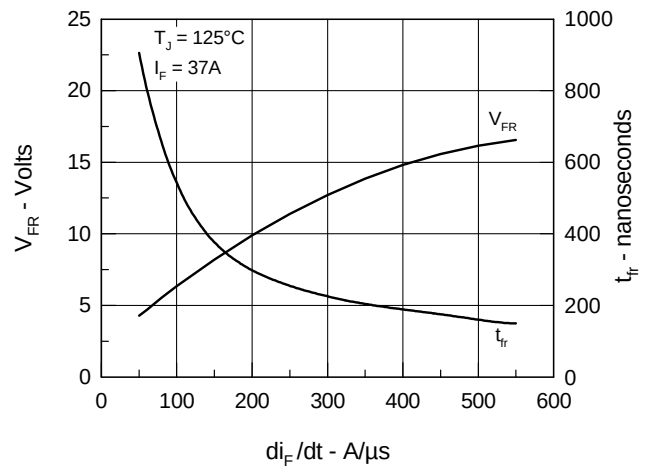
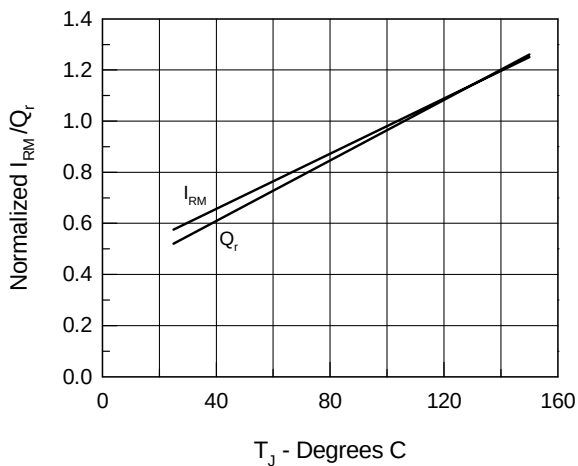
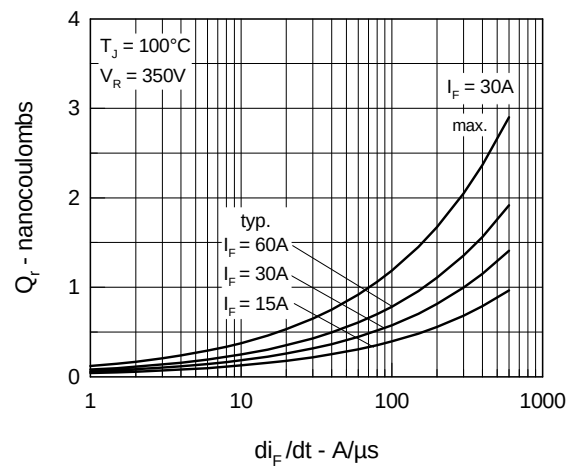
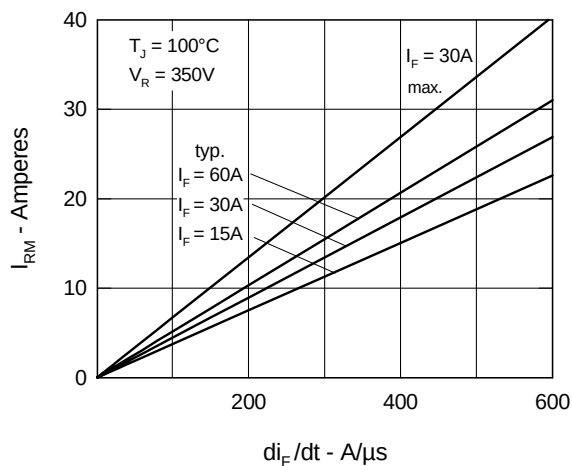
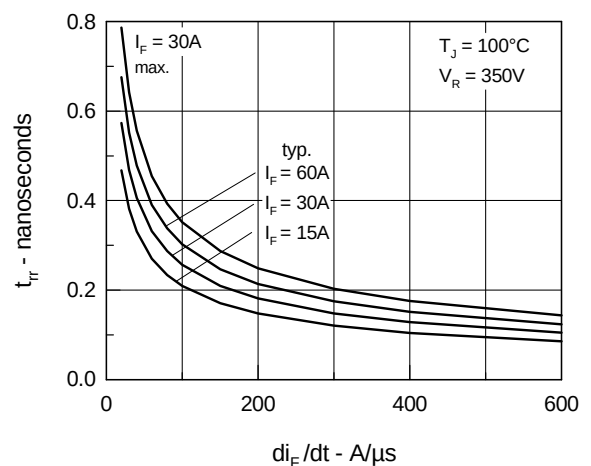
Fig.12 Maximum Forward Voltage Drop

Fig.13 Peak Forward Voltage V_{FR} and Forward Recovery Time t_{fr}

Fig.14 Junction Temperature Dependence of I_{RM} and Q_r

Fig.15 Reverse Recovery Charge Q_r

Fig.16 Peak Reverse Recovery Current

Fig.17 Reverse Recovery Time


Fig.18 Diode Transient Thermal resistance junction to case

